

◆ Features

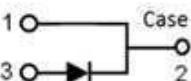
- Negligible reverse recovery
- High-speed switching
- Positive Temperature Coefficient
- Temperature-Independent Switching
- Pb-free / RoHS compliant

650V SILICON CARBIDE
SCHOTTKY DIODE
 V_{RRM} 650V
 I_F 8A ($T_c=150^\circ\text{C}$)
 Q_C 23nC

◆ Benefits

- Higher frequency
- Low heat dissipation requirements
- Reduce size and cost of the system
- High-reliability



TO-247AC
 1 Case
3 2

Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Value | Unit | Note |
|----------------|---------------------------------------|-------------|----------------------|----------|
| V_{RRM} | Repetitise peak reverse voltage | 650 | V | |
| I_F | Continuous forward current | 21 | A | Figure 3 |
| | | 10 | A | |
| | | 8 | A | |
| I_{FSM} | Non-repetitive forward surge current | 74 | A | |
| | | 65 | A | |
| I_{FRM} | Repetitive Peak Forward Surge Current | 66 | A | |
| $\int i^2 dt$ | $i^2 t$ value | 27 | A^2s | |
| | | 21 | A^2s | |
| P_{tot} | Power Dissipation | 86 | W | Figure 4 |
| | | 37 | W | |
| | | 14 | W | |
| T_j, T_{stg} | Operating and Storage Temperature | -55 to +175 | $^\circ\text{C}$ | |

**Electrical Characteristics (T_c=25°C unless otherwise noted)**

| Symbol | Parameter | Test Conditions | Value | | | Unit | Note |
|-----------------|---------------------------|---|-------|------|------|------|----------|
| | | | Min. | Typ. | Max. | | |
| V _{DC} | DC blocking voltage | | 650 | - | - | V | |
| V _F | Forward voltage | I _F =4A | - | 1.18 | - | V | Figure 1 |
| | | I _F =8A, T _c =25°C | - | 1.39 | 1.6 | V | |
| | | I _F =8A, T _c =175°C | | 1.74 | | V | |
| I _R | Reverse current | V _R =650V, T _c =25°C | - | 6 | 60 | uA | Figure 2 |
| | | V _R =650V, T _c =175°C | | 12 | | uA | |
| Q _C | Total capacitive charge | V _R =400V | - | 23 | - | nC | Figure 6 |
| C | Total capacitance | V _R =1V, f=1MHZ | - | 338 | - | pF | Figure 5 |
| | | V _R =200V, f=1MHZ | - | 44 | - | pF | |
| | | V _R =400V, f=1MHZ | - | 43 | - | pF | |
| E _C | Capacitance Stored Energy | V _R =400V | - | 3.8 | - | uJ | Figure 7 |

Thermal Characteristics

| Symbol | Parameter | Value | | Unit | Note |
|----------------------|---------------------------------------|-------|------|------|----------|
| | | Typ. | Max. | | |
| R _{th(j-c)} | Thermal resistance (Junction to case) | 1.734 | - | °C/W | Figure 8 |

Electrical Characteristic Curves

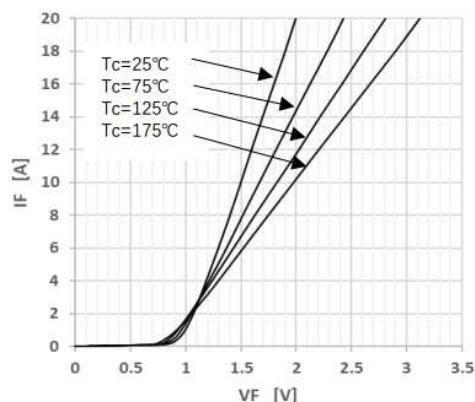


Figure 1 Forward Characteristics

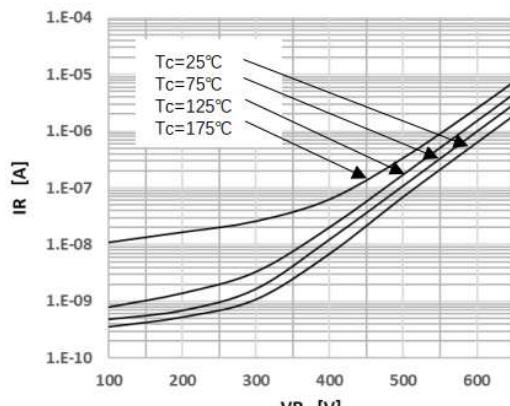


Figure 2 Reverse Characteristics

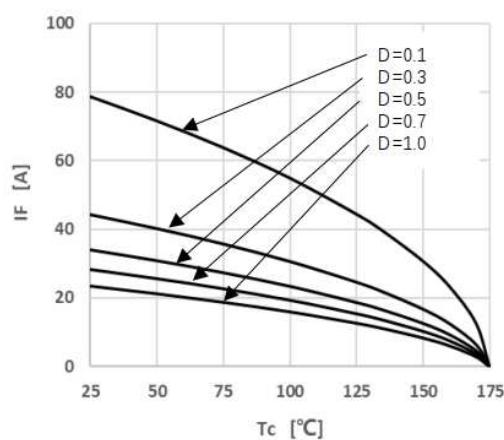


Figure 3 Peak Forward Current Derating

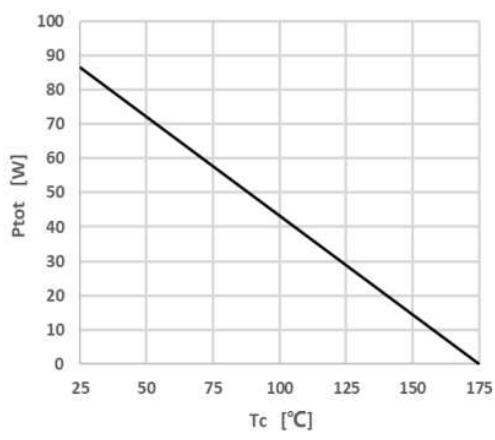


Figure 4 Power Dissipation

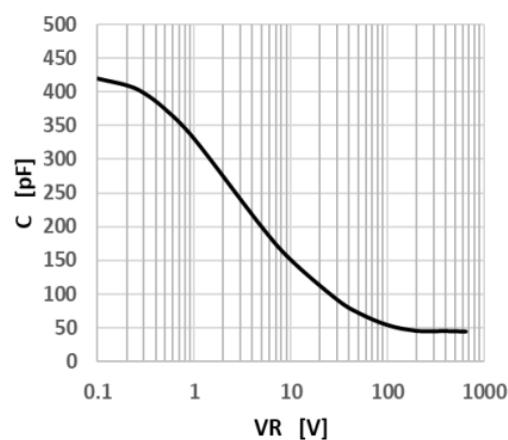


Figure 5 Capacitance vs. Reverse Voltage

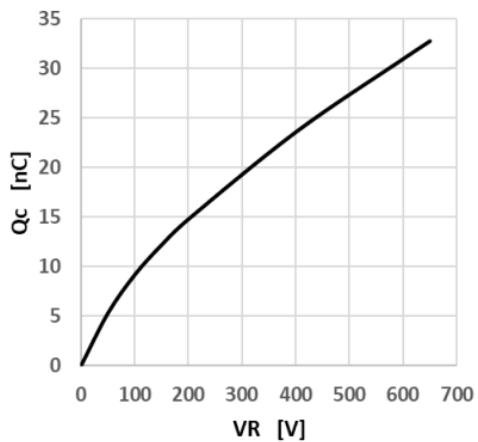


Figure 6 Capacitance Charge vs. Reverse Voltage

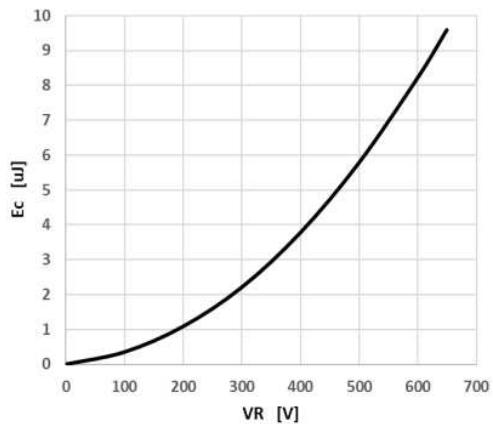


Figure 7 Capacitance Stored Energy

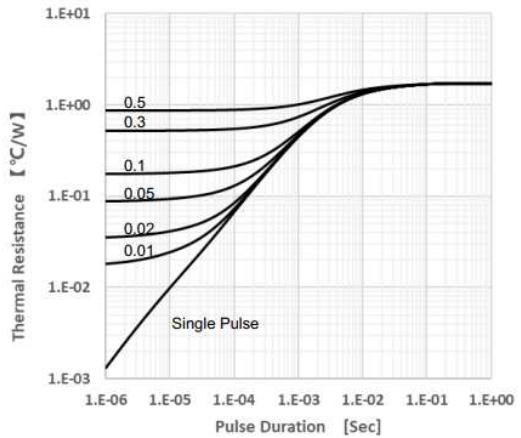
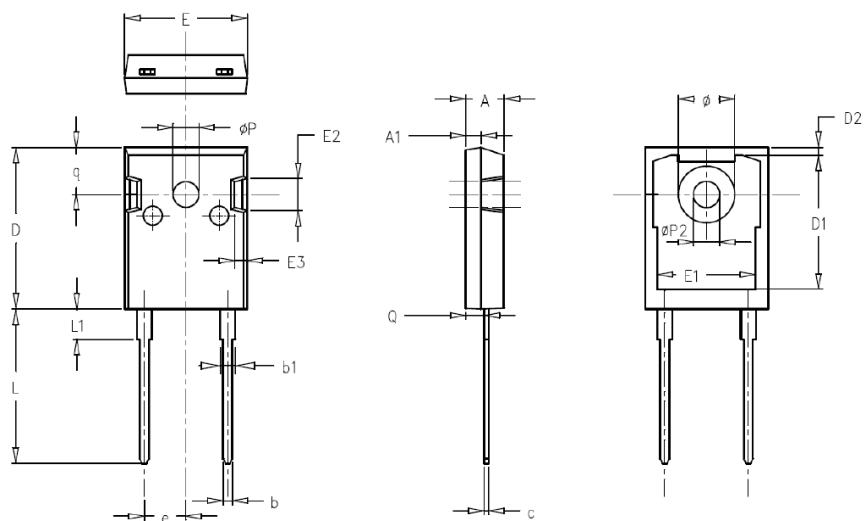


Figure 8 Transient Thermal Impedance

TO-247AC Package Dimensions : (Unit : mm)



| SYMBOL | MILLIMETERS | | | N O T E S | SYMBOL | MILLIMETERS | | | N O T E S |
|--------|-------------|---------|---------|-----------|--------|-------------|---------|---------|-----------|
| | N o r m a l | M I N . | M A X . | | | N o r m a l | M I N . | M A X . | |
| A | 4.98 | 4.68 | 5.36 | | φP | 3.66 | 3.45 | 3.85 | |
| A1 | 1.99 | 1.90 | 2.10 | | e | 5.44 | BSC | | |
| Q | 2.41 | 2.30 | 2.60 | | q | 6.24 | 5.99 | 6.58 | |
| c | 0.60 | 0.48 | 0.72 | | φP2 | 3.45 | 3.24 | 3.64 | |
| b | 1.20 | 1.00 | 1.40 | | φ | 7.14 | 7.10 | 7.30 | |
| b1 | 2.07 | 1.90 | 2.30 | | D1 | 16.56 | 16.10 | 17.10 | |
| D | 21.10 | 20.80 | 21.80 | | D2 | 0.98 | 0.80 | 1.36 | |
| E | 15.98 | 15.38 | 16.20 | | E1 | 13.30 | 13.00 | 13.52 | |
| L | 20.28 | 19.50 | 20.50 | | E2 | 5.64 | 5.10 | 6.10 | |
| L1 | 4.01 | 3.75 | 4.35 | | E3 | 2.33 | 1.90 | 2.70 | |